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3-6-03  
J. Carter

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Lin et al.

Art Unit: 2814

Serial No.: 09/975,444

Examiner: Pham, L.

Filing Date: 10/11/2001

Docket No.: TI-31518

Title: ELIMINATION OF OVERHANG IN LINER/BARRIER/  
SEED LAYERS USING POST-DEPOSITION SPUTTER ETCH**Amendment under 37 CFR 1.111**

Assistant Commissioner of Patents  
Washington, DC 20231

Dear Sir:

The following amendments and remarks are offered in response to the Examiner's Office Action dated 11/04/2002. They are respectfully submitted as a full and complete response to that Action.

Please amend the above-referenced application as follows:

**In the Claims:**

Replace claim 1 with the following claim:

1. (amended) A method of fabricating an integrated circuit, comprising the steps of:
- forming a dielectric layer over a semiconductor body;
  - forming a hole in said dielectric layer;
  - depositing a metal layer over said dielectric layer including in said hole using physical vapor deposition;
  - performing a sputter etch using a low bias after said step of depositing the metal layer; and
  - then, depositing a metal filler to fill said hole.